

AMENDMENTS TO THE CLAIMS

Please amend the present application as follows:

Claims

1- 4. (Canceled)

5. (Currently amended) A packaging device for a semiconductor die, the packaging device comprising:

a substantially planar substrate having opposed major surfaces;

an electrically conductive die mounting pad located on one of the major surfaces of the substrate, the conductive die mounting pad dimensioned to accommodate the die with a major surface of the die in contact therewith;

a first electrically conductive connecting pad located on the other of the major surfaces of the substrate, the first electrically conductive connecting pad dimensioned to conform to an industry standard pad layout of a printed circuit board;

a The packaging device of claim 1, in which the first electrically conductive interconnecting element comprises tungsten interconnecting element extending through the substrate and electrically interconnecting the mounting pad and the connecting pad.

6- 21. (Canceled)

22. (Currently amended) A semiconductor device, comprising:

a substantially planar substrate having opposed major surfaces;

an electrically conductive mounting pad located on one of the major surfaces of the substrate;

The semiconductor device of claim 21 wherein the semiconductor die comprises a light emitting diode (LED) having a metallized bottom major surface that is mounted on the electrically conductive mounting pad, and the metallized bottom major surface comprises comprising one of an anode and a cathode of the LED;

a first electrically conductive connecting pad located on the other of the major surfaces of the substrate; and

a first electrically conductive interconnecting element extending through the substrate and electrically interconnecting the mounting pad and the first electrically

conductive connecting pad.

23. (Currently amended) The semiconductor device of claim 21 22, further comprising:
an electrically conductive bonding pad located on the one of the major
surfaces of the substrate;

a bonding wire extending between a metallized top major surface of the
~~semiconductor die~~ LED and the electrically conductive bonding pad;

a second electrically conductive connecting pad located on the other of the
major surfaces of the substrate; and

a second electrically conductive interconnecting element extending through
the substrate and electrically interconnecting the bonding pad and the second connecting pad.

24. (Currently amended) The semiconductor device of claim 23 wherein the
~~semiconductor die comprises a light emitting diode (LED)~~, the metallized top major surface
comprises a first electrode of the LED and the metallized bottom major surface comprises a
second electrode of the LED.

25. (Currently amended) The semiconductor device of claim 21 22 wherein the first
electrically conductive interconnecting element is selected to withstand an operating
temperature when the ~~semiconductor die~~ LED is mounted on the electrically conductive
mounting pad and to provide a low-resistance electrical connection between the mounting
pad and the first electrically conductive connecting pad.

26. (Previously presented) The semiconductor device of claim 25, wherein the first
electrically conductive interconnecting element comprises tungsten.

27. (Previously presented) The semiconductor device of claim 25, wherein the first
electrically conductive interconnecting element comprises a slug of electrically conductive
material, the slug having a diameter selected to press-fit the slug into a through hole located
in the substrate between the mounting pad and the first electrically conductive connecting
pad.